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# Source radiance requirements for high-resolution imaging and interference techniques



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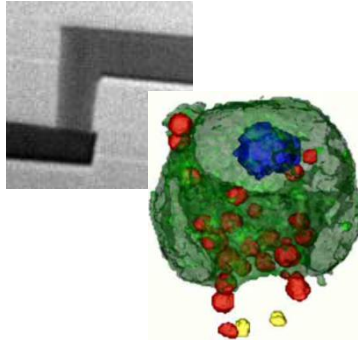


# Applications summary

XUV: short wavelength and strong light matter interaction

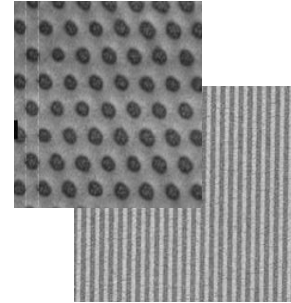


lateral & in-depth (3d) nm resolutions with element sensitivity and high throughput



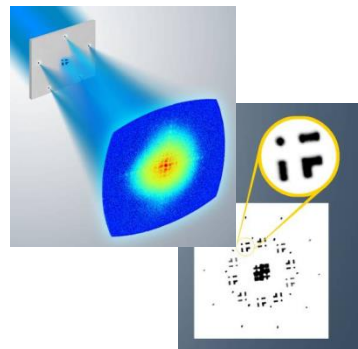
## Microscopy

- 3d imaging (cells, electronics)
- “no” sample preparation
- several  $\mu\text{m}$  penetration depths
- magnetic (spin) contrast with polarized light



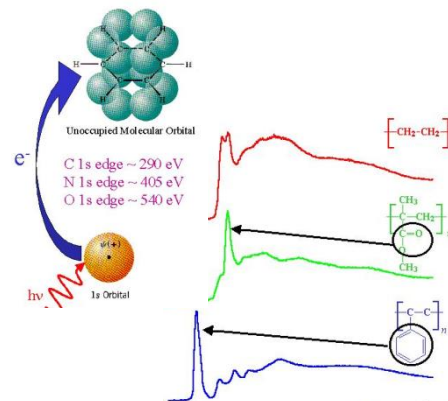
## Patterning

- high density arrays
- large exposition areas
- access to  $< 10$  nm scale
- negligible proximity effect
- independent on substrate



## Scatter/diffractometry

- nano-roughness
- nano-structures arrays
- nano-defect inspection
- lens less imaging with coherent light



## Spectroscopies

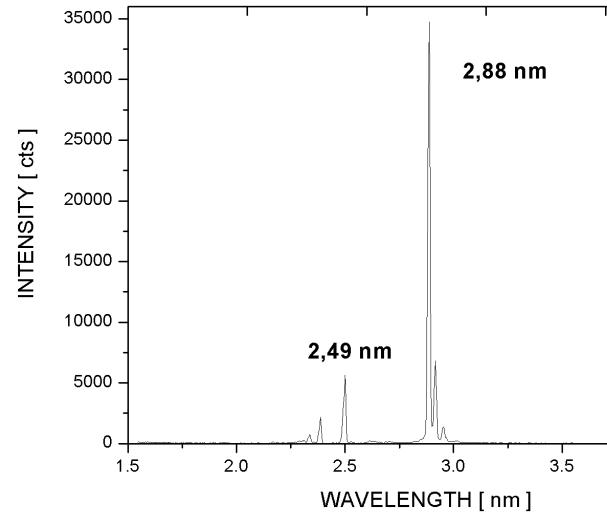
- element selectivity
- chemical bonding (NEXAFS)
- small penetration depths of radiation ( $< 100$  nm)
- large grazing incidence angle

# EUV and soft x-ray microscopy: element-sensitive contrast and high spatial resolution (down to ~10 nm)

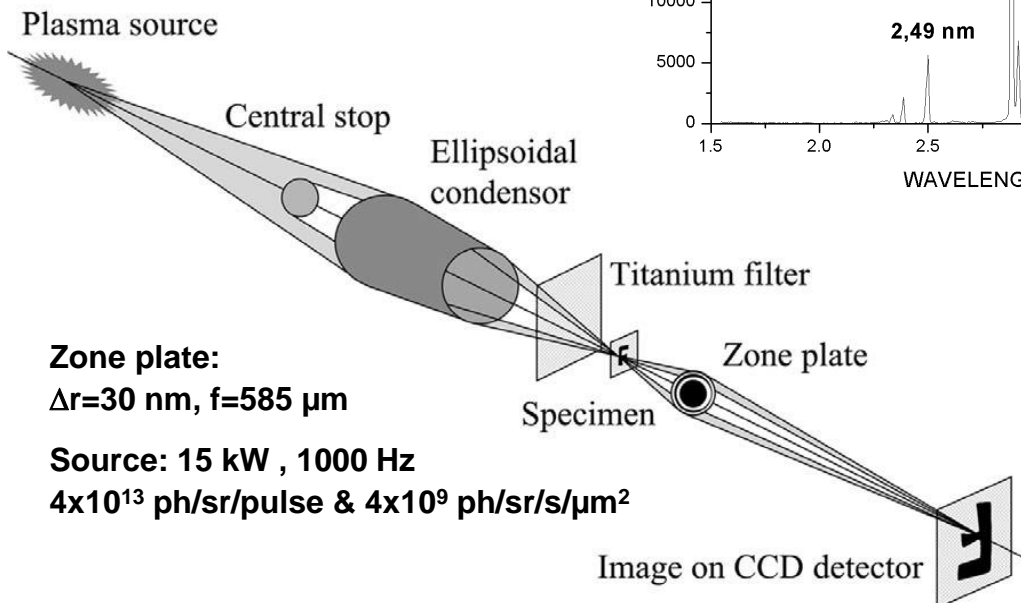
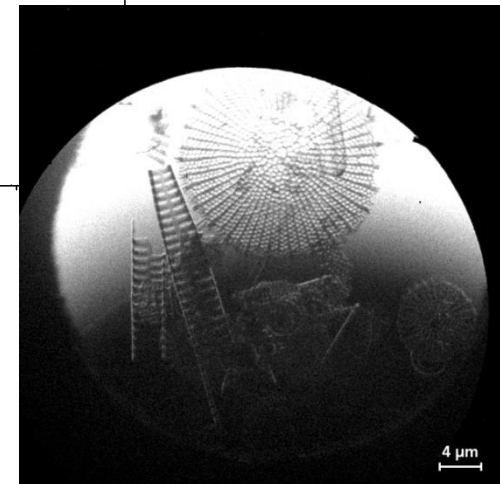
## Discharge Source

Working gas: Nitrogen

28 W/sr/cm<sup>2</sup> @ single line at 2.88 nm



Diatom in bright- and dark field illumination mode (due to special illumination of the zone plate)



Zone plate:

$\Delta r = 30$  nm,  $f = 585$  μm

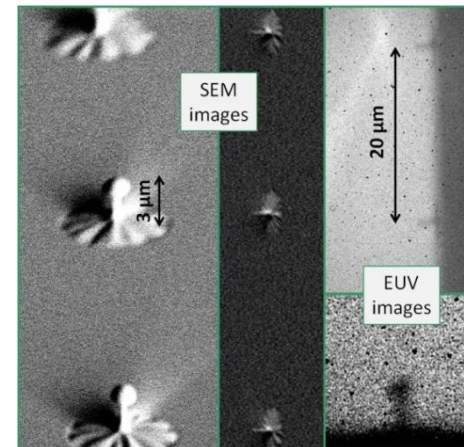
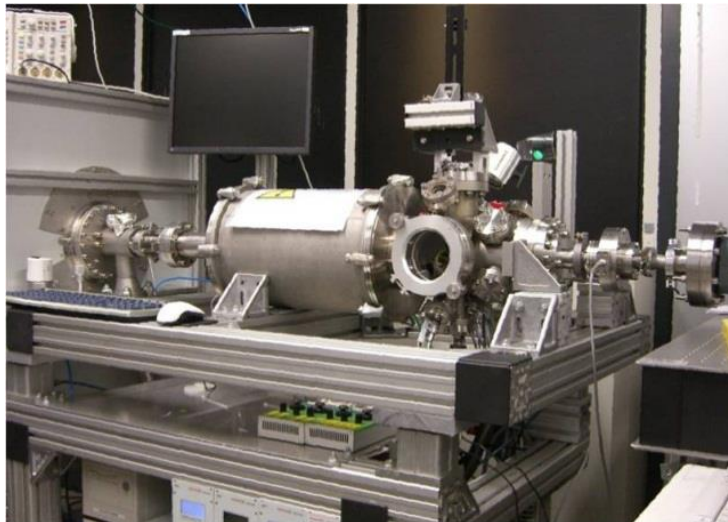
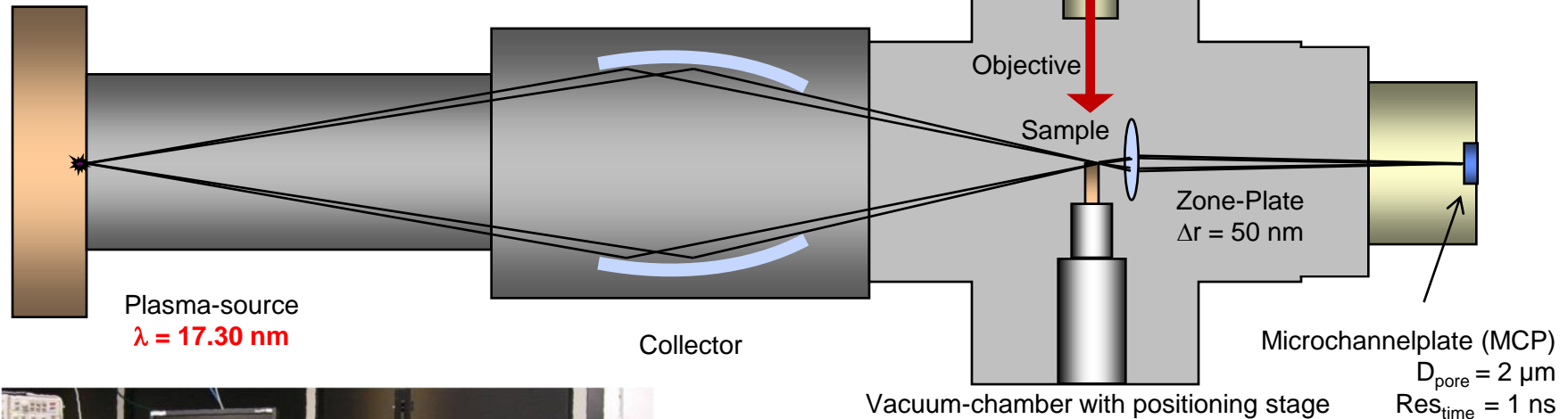
Source: 15 kW, 1000 Hz

$4 \times 10^{13}$  ph/sr/pulse &  $4 \times 10^9$  ph/sr/s/μm<sup>2</sup>

Courtesy of K. Bergmann, M. Benk, FhG ILT, and Th. Wilhein, D. Schäfer, FH Remagen

# Pump & probe microscope

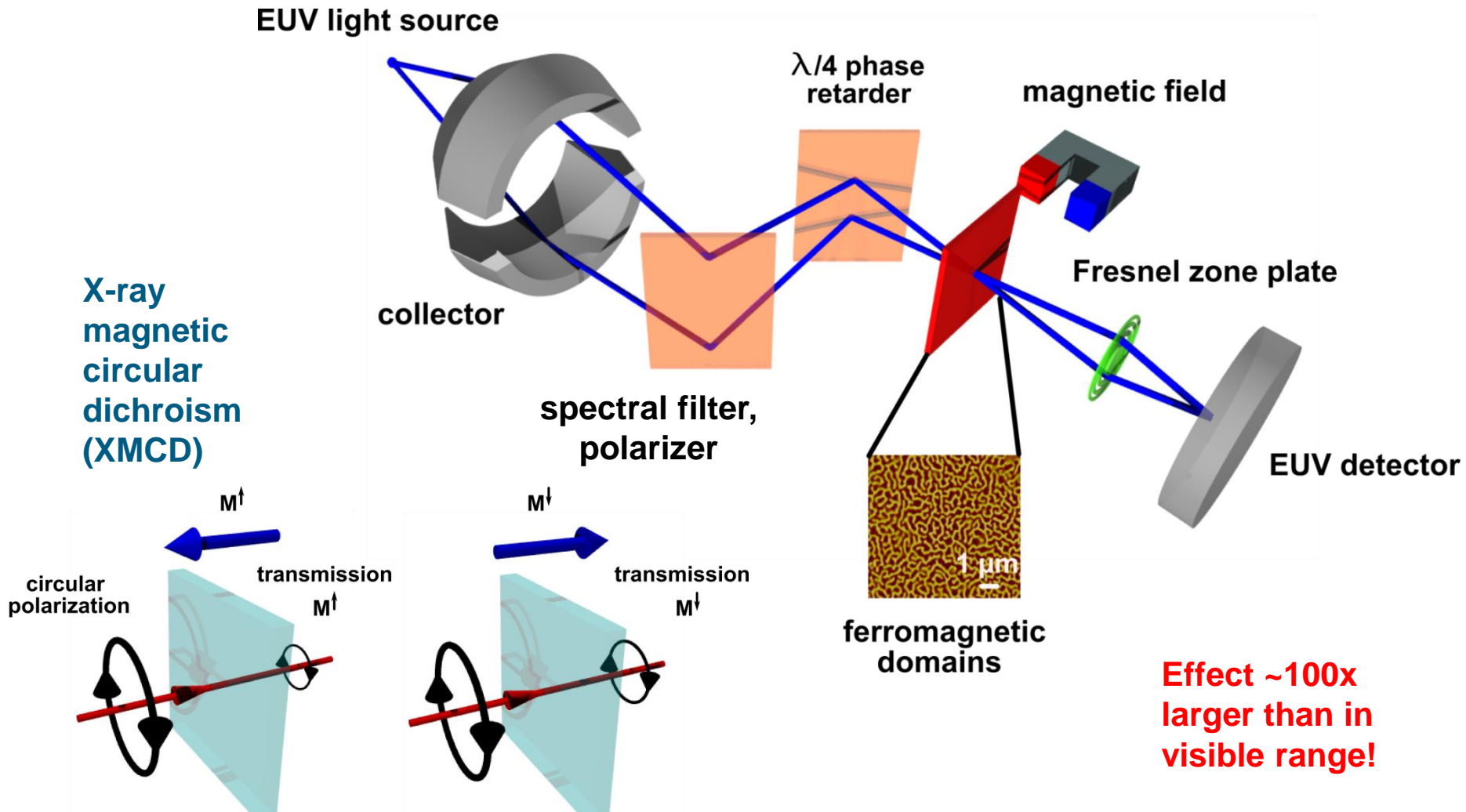
## Scheme of the EUV-Microscope



Nano-jets from  
Au thin film  
induced by a  
femtosecond  
laser pulse

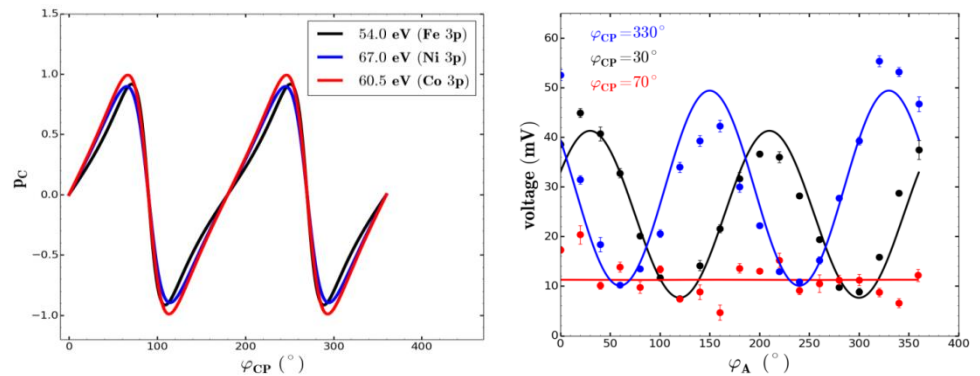
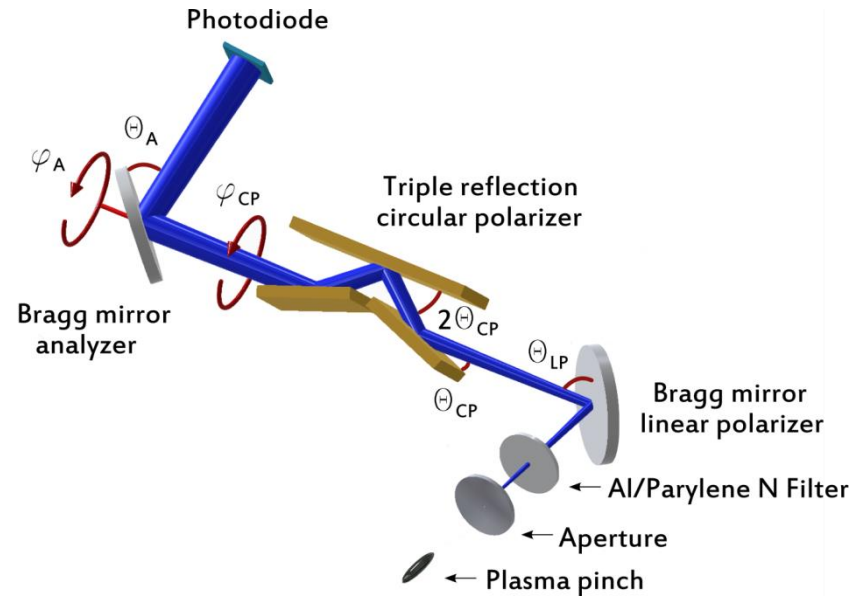
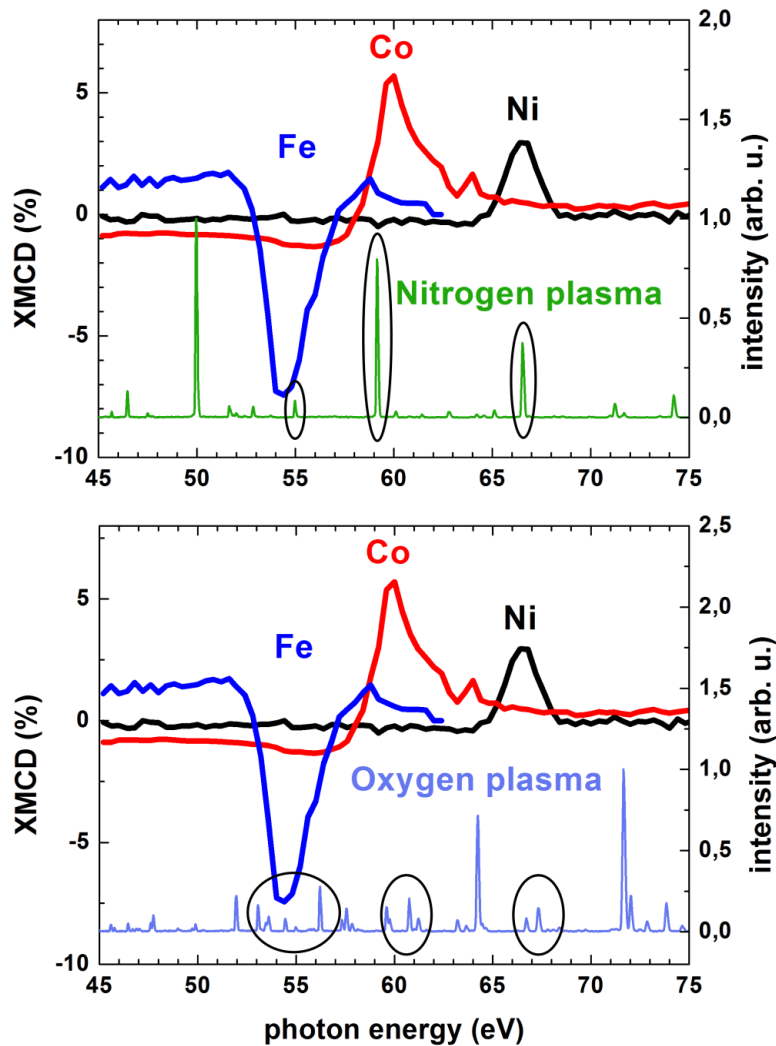
$M = 375$   
 $\text{RES} = 75 \text{ nm}$

# Magneto-optical microscope





# XMCD-contrast at 3p edges of Fe, Co and Ni

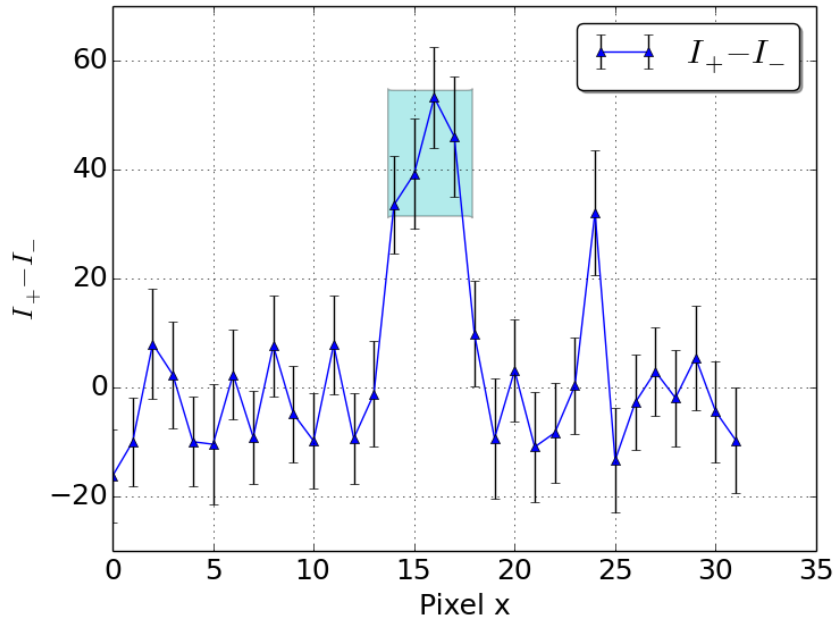


D. Wilson, D. Rudolf, et al., Review of Scientific Instruments 85, 103110 (2014)

# XMCD at Co 3p absorption edge

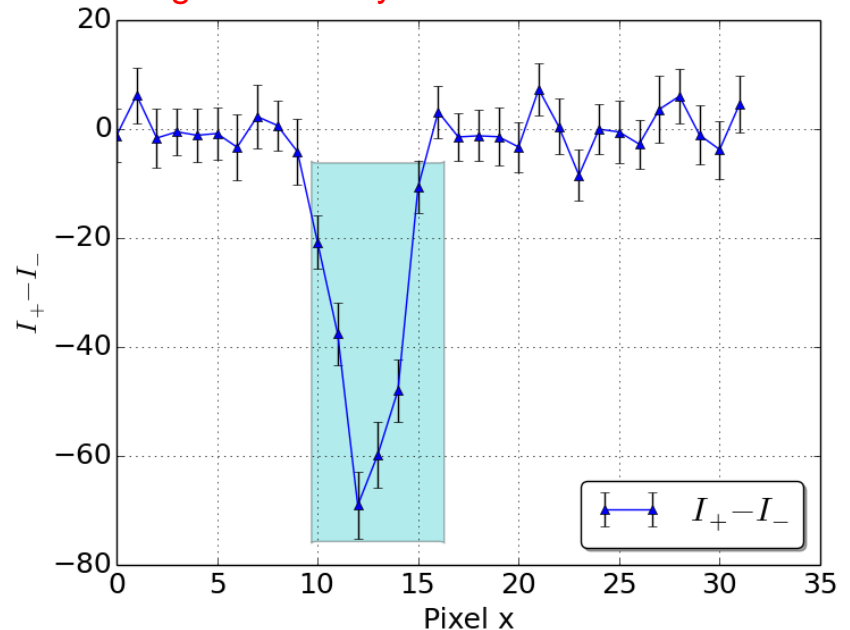
Sample: [Co (0.8 nm) / Pt (1.4 nm)]<sub>16x</sub>

Positive helicity



$$A = \frac{T_+ - T_-}{T_+ + T_-} = (2.7 \pm 0.1)\%$$

Negative helicity



$$A = \frac{T_+ - T_-}{T_+ + T_-} = (-2.8 \pm 0.1)\%$$

D. Wilson, D. Rudolf, et al., Review of Scientific Instruments 85, 103110 (2014)

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# Photon detections: required flux based on contrast

**Contrast:**

$$C = \frac{\text{signal difference}}{\text{background}} = \frac{n_{ph\_f} - n_{ph\_b}}{n_{ph\_b}}$$

**Sensitivity index:**

$$d' = \frac{\text{separation}}{\text{spread}} = \frac{n_{ph\_f} - n_{ph\_b}}{\sqrt{n_{ph\_b}}}$$

$d'$  of at least 5 is needed for 100% certainty in distinguishing image features

“Signal Detection Theory” or A. Rose, “Television pickup tubes and the problem of vision”, Advances in Electronics **1**, 131-166 (1948)

Quasi-ideal detector (signal noise dominating):

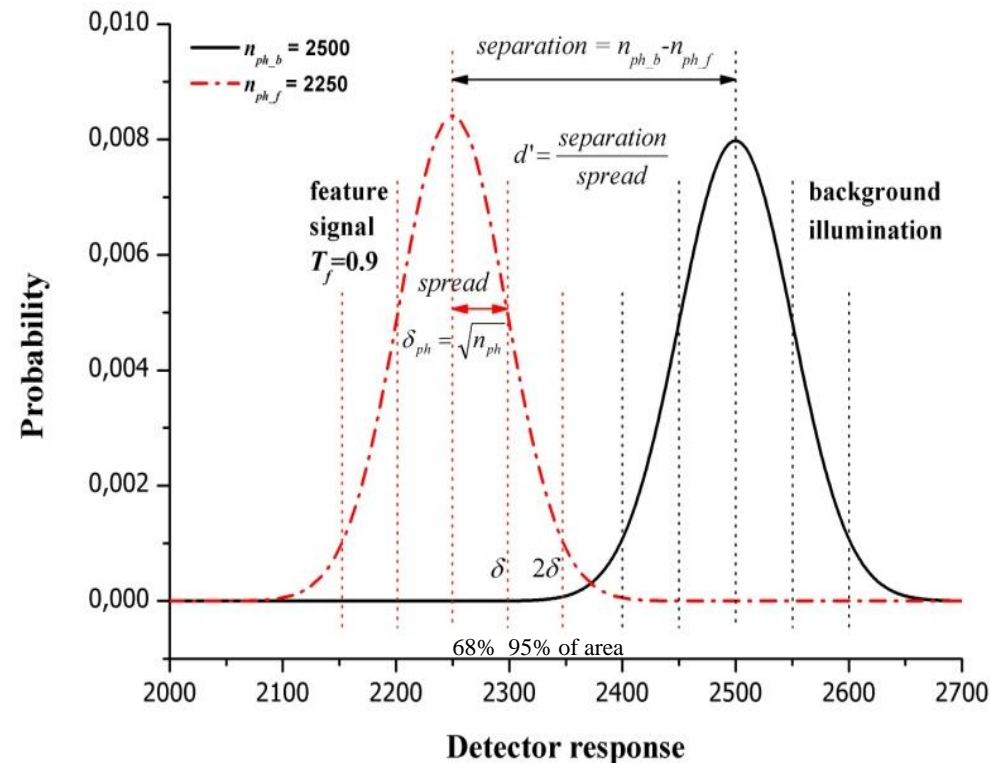
$$d'_{\text{det}} = \sqrt{QE} \cdot d'$$

Required number of photons:

$$n_{ph\_b} \geq \frac{25}{QE \cdot C^2}$$

photon detections → Poisson statistics

Photon noise:  $\delta_{ph} = \sqrt{n_{ph}}$





# Source radiance and etendue

Spectral radiance: radiation energy (photons) per time interval, wavelength, solid angle and area

$$\text{Radiance} = \frac{\text{photon flux}}{\text{etendue}}$$

$$L = \frac{d^2\Phi}{dA \cdot \cos \theta \cdot d\Omega} = n^2 \cdot \frac{d^2\Phi}{d^2G}$$

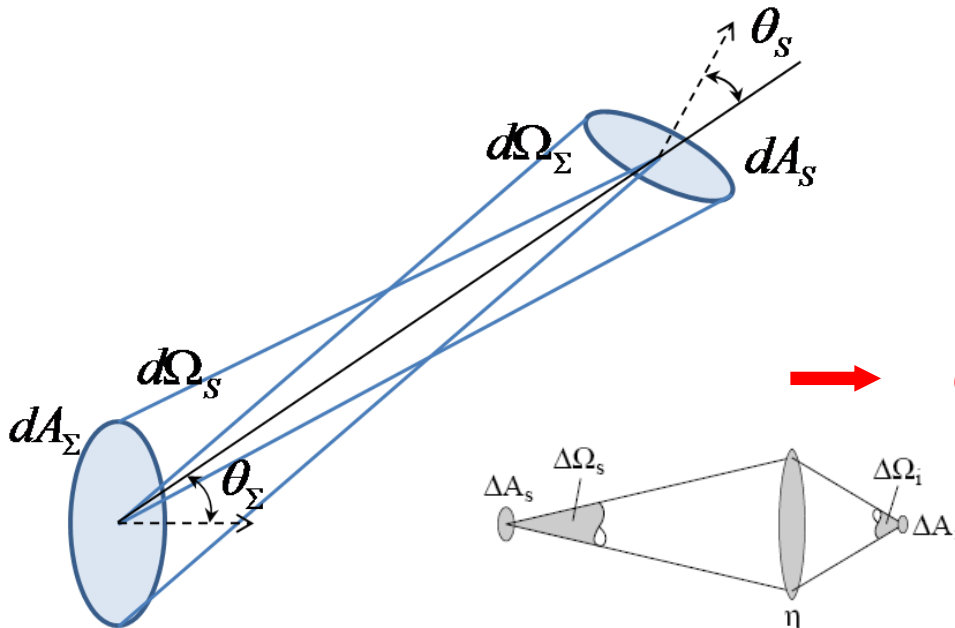
*not increasing* (pointing to Radiance)  
*not increasing* (pointing to photon flux)  
*not decreasing* (pointing to etendue)

Etendue

$$G = \iint_{A \Omega} dA \cos \theta \cdot d\Omega = \pi \cdot NA^2 \cdot A$$

**NA** – numerical aperture  
**A** – field of view area

**constant in optical system (at best)**

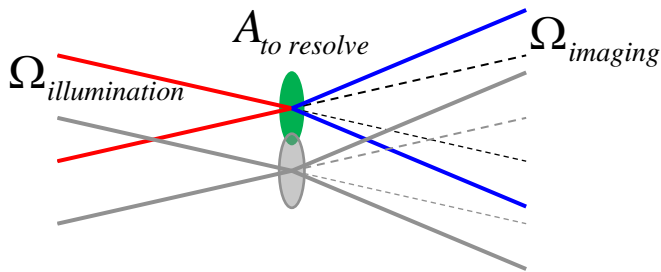


$$\Delta A_s \cdot \Delta \Omega_s = \Delta A_i \cdot \Delta \Omega_i; \eta = 100\%$$

# Requirements on source radiance

At sample:

$$n_{ph\_b}, t_{exposure}, \Omega_{illumination}, A_{to\ resolve} \Rightarrow L_{sample} = \frac{n_{ph\_b} \cdot E_{ph}}{t_{exposure} \cdot \Omega_{illumination} \cdot A_{to\ resolve}}$$



Transmission of the system:  $T_{system}$

$$\Rightarrow L_{source} = \frac{n_{ph\_b} \cdot E_{ph}}{T_{system} \cdot t_{exposure} \cdot \Omega_{illumination} \cdot A_{to\ resolve}}$$

$$L = \frac{25 \cdot hc / \lambda}{QE \cdot C^2 \cdot T_{system} \cdot t_{exposure} \cdot \Omega_{illumination} \cdot A_{to\ resolve}}$$

Resolution matched imaging:  $A_{to\ resolve} \cong \left( \frac{\lambda}{2 \cdot NA_{imaging}} \right)^2$

$$\Omega_{illumination} = \pi \cdot NA_{ill}^2 \Rightarrow L \cong \left( \frac{NA_{im}}{NA_{ill}} \right)^2 \frac{25 \cdot hc}{QE \cdot C^2 \cdot T_{sys} \cdot t_{exp} \cdot \lambda^3} \cong 5 \cdot 10^{-3} \frac{NA_{im}^2 / NA_{ill}^2}{QE \cdot C^2 \cdot T_{sys} \cdot t_{exp} [s] \cdot \lambda^3 [nm]} \frac{W}{mm^2 \cdot sr}$$

Bright field imaging:  $NA_{im}=NA_{il}$

wavelength 2.88 13.5 nm

contrast -0.1 -0.2

T system 1 2 %

exposure 1 0.1 s

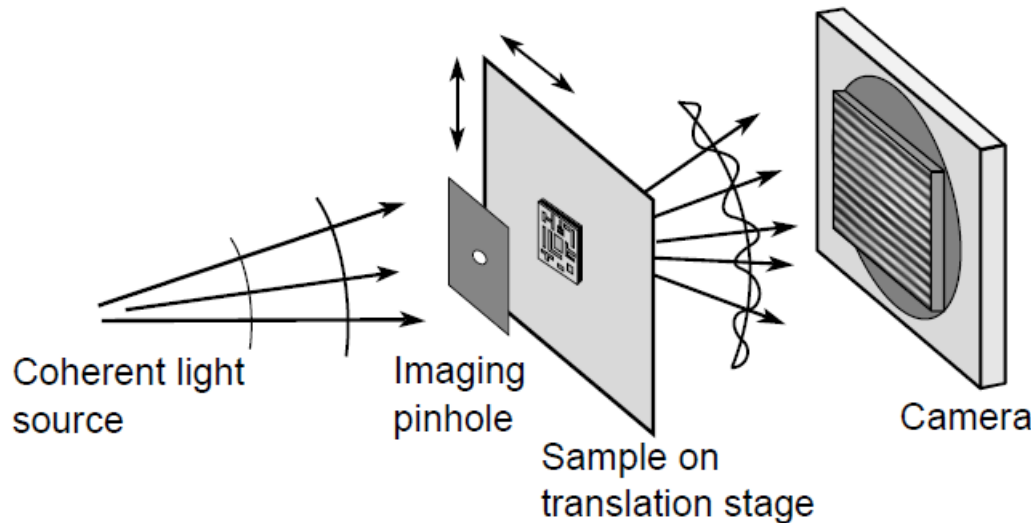
**radiance 4 0.05 W/mm<sup>2</sup>/sr**

# Laboratory-scale lens-less EUV imaging

## Gains compared to standard lens-based microscopy

- Not limited by quality of optics
- More compact setup, easier alignment
- Better use of incidence light => lower dose
- Reconstruction of phase shift and attenuation

**particularly suited for  
imaging with short  
wavelength radiation**

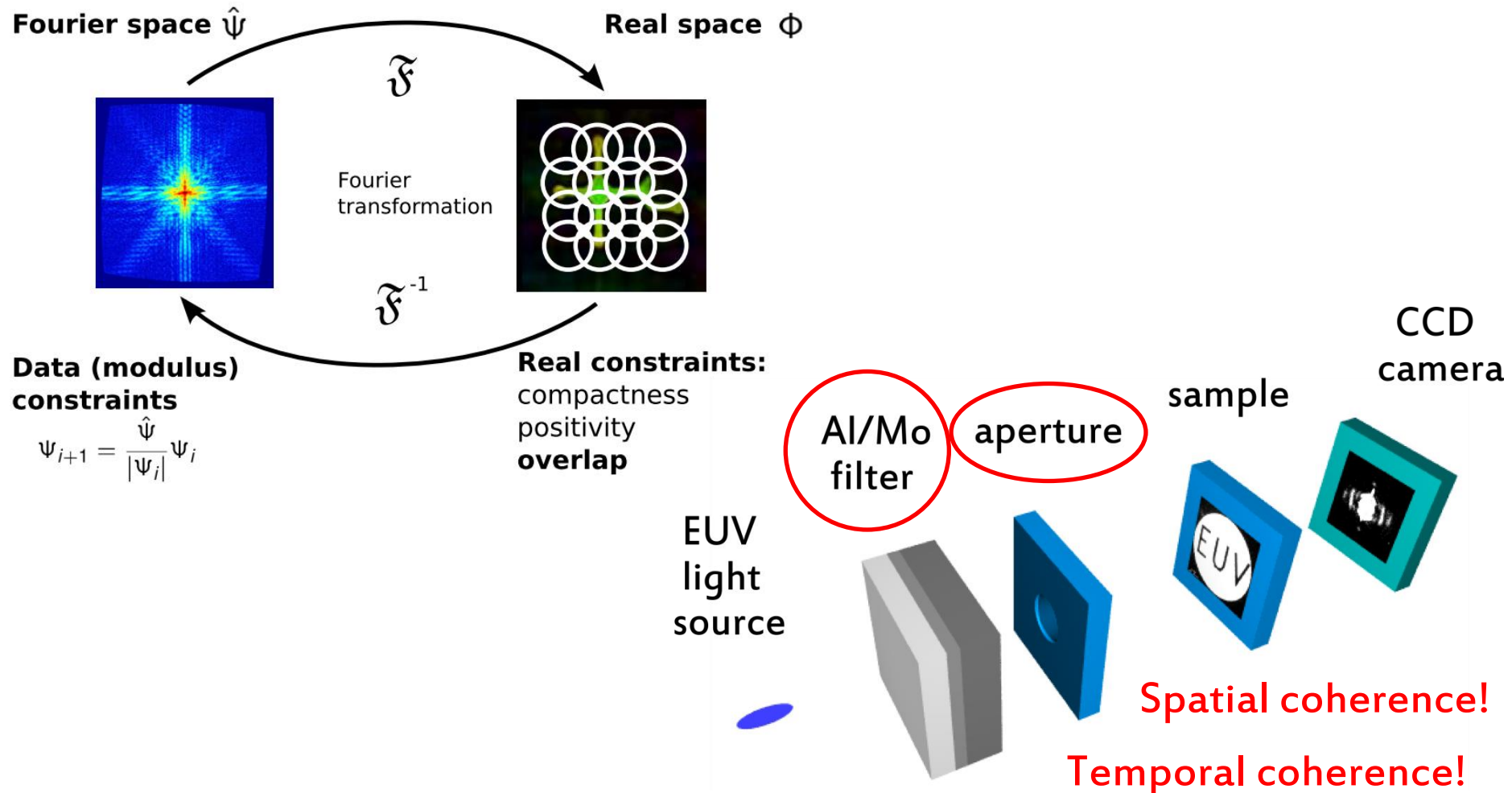


**XUV: short wavelength  
and strong light matter  
interaction**



**lateral & in-depth (3d)  
nm resolutions with  
element sensitivity and  
high throughput**

# Basic principle for coherent imaging & experimental setup

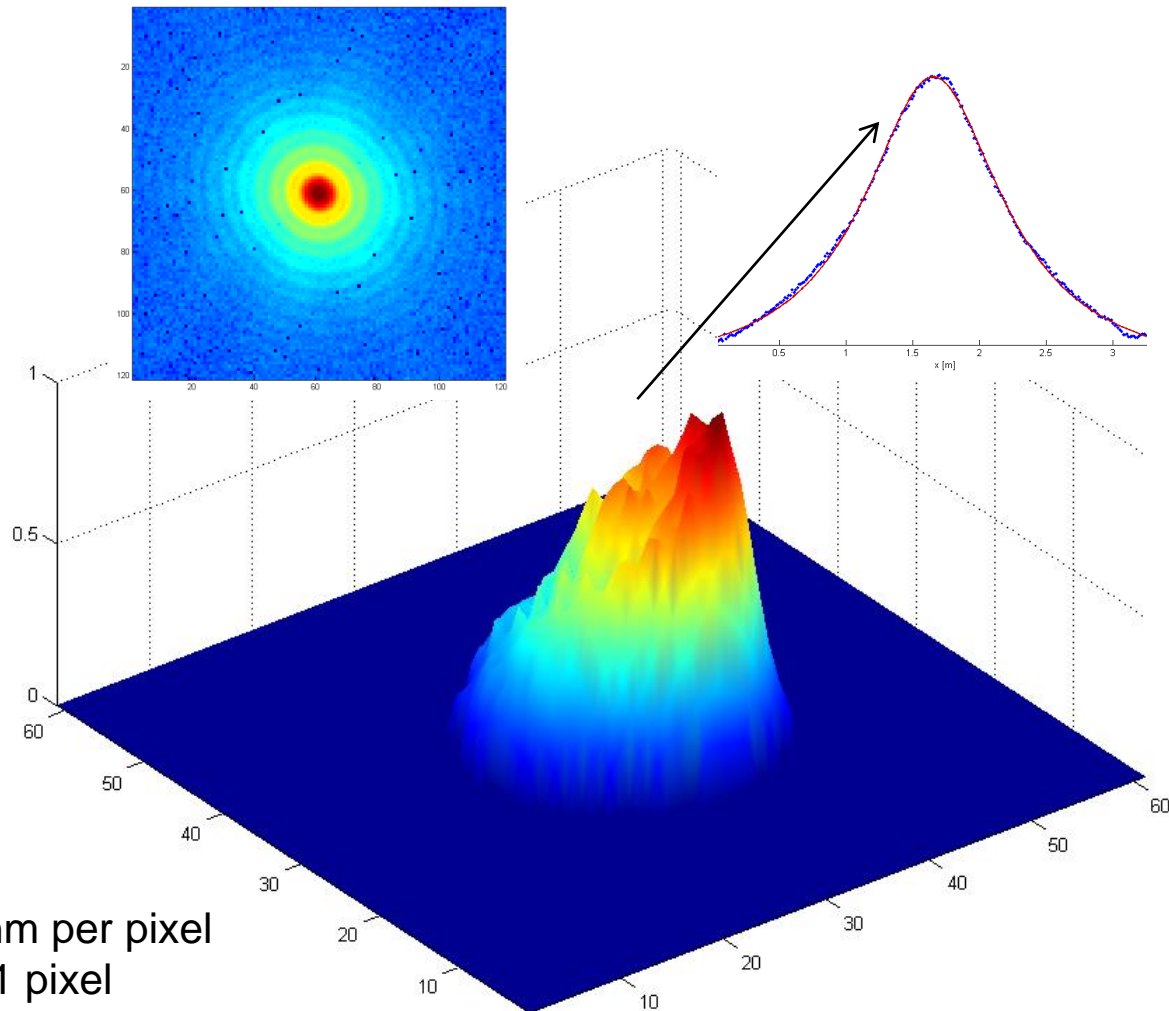


# Reconstruction procedure and result: illumination wave front

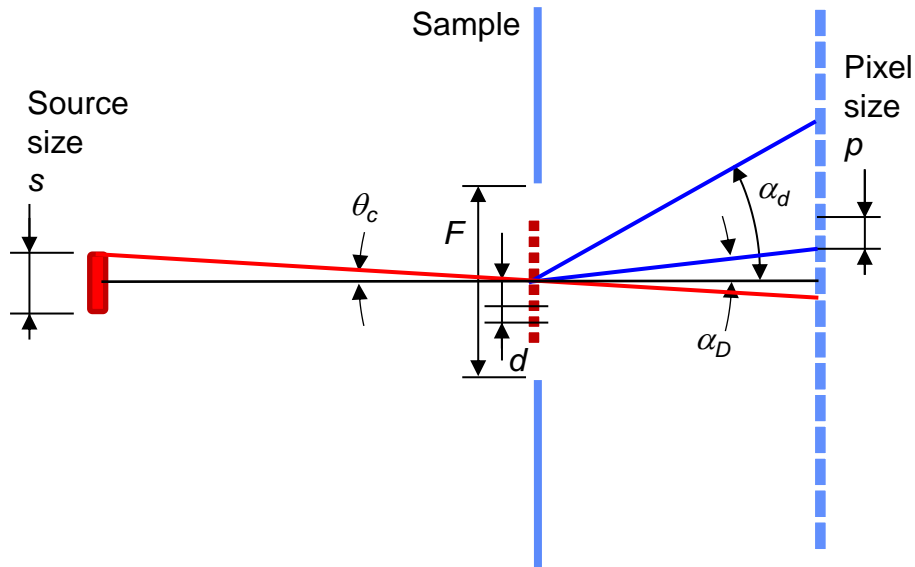
1. Background subtraction
2. Hot pixel detection
3. Data binning (5x5)
  - > oversampling ratio reduction
  - > dynamic / SNR enhancement
- (4. Symmetrizing)

5. Applying OSS algorithm  
(HIO + filtering outside of support) -> 128 independent runs
6. Averaging of the top 5 images with lowest error ( $R_{\text{factor}}=12.8\%$ )
7. Size determination from experimental distances: pinhole diameter:  $11.2\ \mu\text{m}$

488 nm per pixel  
61x61 pixel



# Coherence and radiance requirements for lens-less imaging



Different spatial frequencies  $1/d$  are present at sample

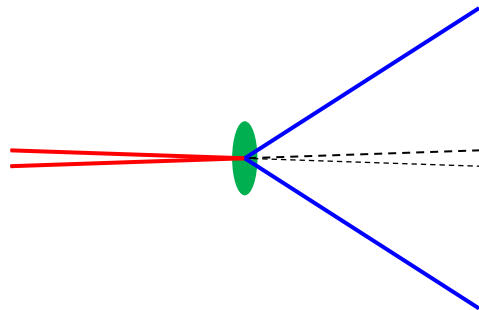
Diffraction angle  $\sin \alpha_d = \lambda / d$

Oversampling  $O > 2$  is required for reconstruction

**Resolution is determined by detector numerical aperture**

Field size and oversampling determine minimum pixel numerical aperture

**Number of pixels in image is determined by bandwidth:**  $N_{\text{pixel}} = \frac{\lambda}{\Delta \lambda} \cdot \frac{1}{O}$



$$\frac{NA_{\text{imaging}}}{NA_{\text{illumination}}} = O \cdot N_{\text{pixel}}$$

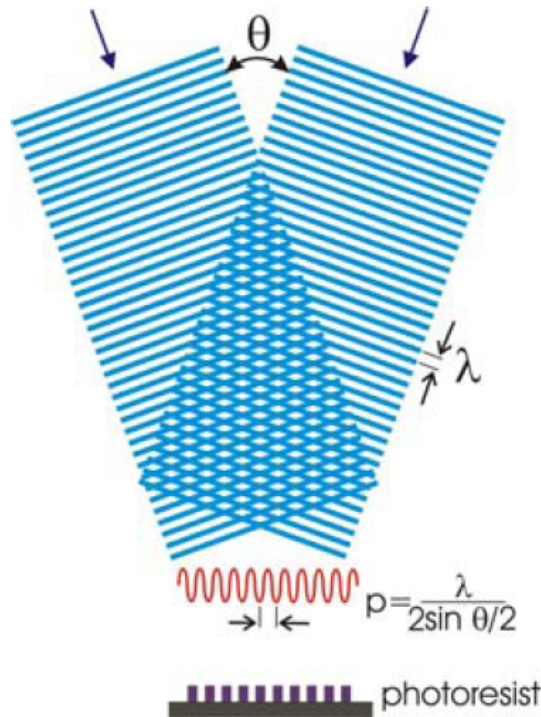
$$\Rightarrow L = \frac{O^2 \cdot N_{\text{pixel}}^2 \cdot 25 \cdot hc}{QE \cdot C^2 \cdot T_{\text{sys}} \cdot t_{\text{exp}} \cdot \lambda^3}$$

phase and amplitude

better compared to lens-based imaging



# Interference lithography



- Large-area periodic structures
- Large depth of focus
- Requires a coherent light
- Low cost – no complicated and expensive optics
- Ultimate resolution (half-pitch) for the wavelength  $\sim \lambda/4$

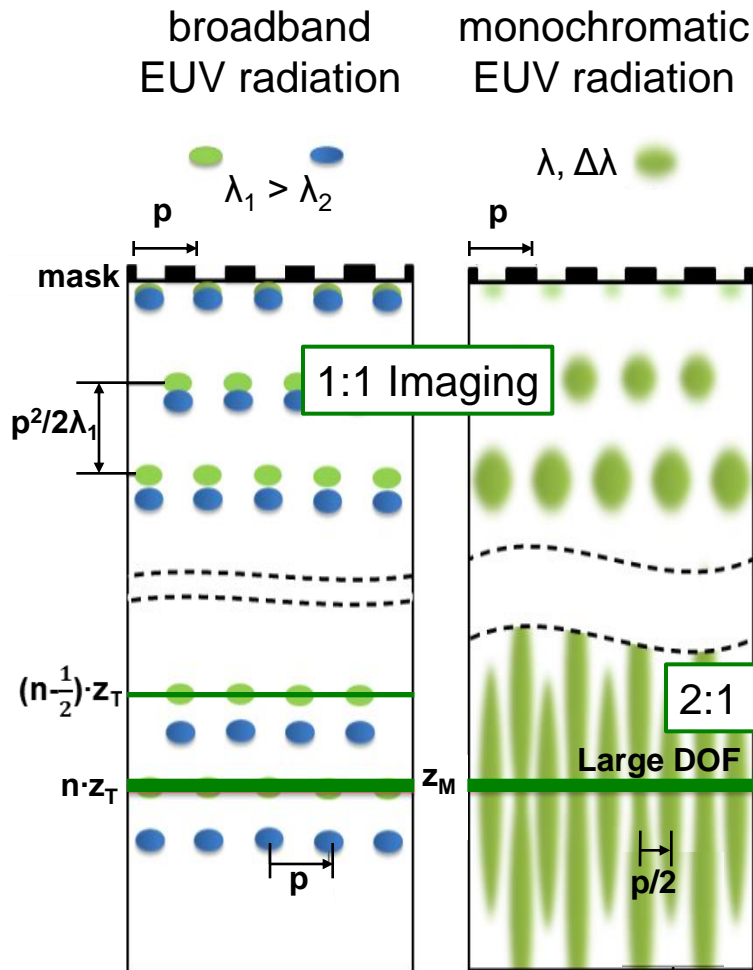
**EUV:  $\lambda = 11 \text{ nm}$  ➡ feature size:  $\sim 3 \text{ nm}$**

**EUV-IL: high resolution, scalable throughput, simple optical system, negligible proximity effect, no charging effects**

## Applications:

- templates for guided self-assembly
- nano-optics, meta-materials
- ultra high density patterned magnetic media
- quantum dot 2D and 3D arrays, nanowire arrays

# Talbot self-imaging, 2:1 pattern demagnification



Achromatic Talbot self-imaging:

- Demagnification of pattern by up to a factor of 2
- Large depth of field

Required spatial coherence for achromatic Talbot self-imaging:

$$I_{\text{coh}} = 4p\lambda/\Delta\lambda$$

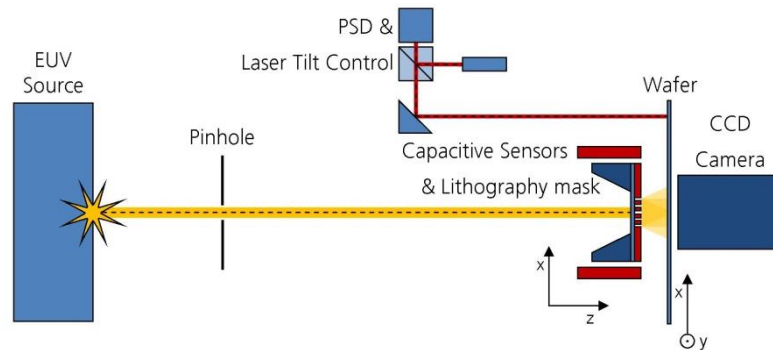
$p$  period for I/s or pinhole grating,  $\lambda$  illumination wavelength,  $\Delta\lambda$  bandwidth of radiation

Talbot distance:

monochromatic:	$n \cdot Z_T = 2p^2/\lambda$
achromatic:	$Z_M = 2p^2/\Delta\lambda$

Example:  $n=1$ ,  $p=100 \text{ nm}$ ,  $\lambda=10.9 \text{ nm}$ ,  $\Delta\lambda/\lambda=3.2\%$   
 monochromatic:  $Z_T=1.83 \text{ }\mu\text{m}$   
 achromatic:  $Z_M=57.33 \text{ }\mu\text{m}$

# EUV laboratory exposure tool – technical specifications



S. Brose, S. Danylyuk, L. Juschk, D. Grützner *et al*, Thin Solid Films 520, 5080 (2012)

- Cleanroom class 100 (ISO 3) environment
- High power EUV discharge produced plasma source:
  - ➔ Optimized emission spectrum with a peak wavelength at  $\lambda = 10.9 \text{ nm}$  and a spectral bandwidth of 3.2%
  - ➔ Up to  $100 \text{ W}/(\text{mm}^2\text{sr})$  radiance at  $10.9 \text{ nm}$
- Illumination schemes: proximity printing and Talbot interference lithography
- Accepts up to 100 mm wafer
- Max. exposable area:  $65 \times 65 \text{ mm}^2$
- Single field:  $2 \times 2 \text{ mm}^2$
- EUV sensitive CCD camera
- High precision positioners on all axes (encoder resolution  $< 10 \text{ nm}$ )
- Dose monitor for  $\lambda = 13.5 \text{ nm}$

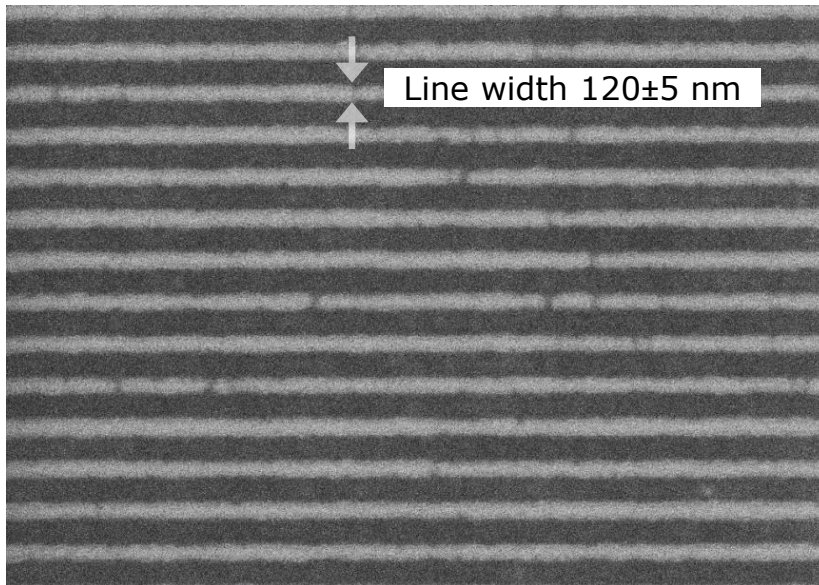
# Exposure results EUV-LET

## Lines and spaces pattern (half-pitch 100/50 nm)

Proximity printing

Half-pitch 100 nm, distance  $z \approx 0 \mu\text{m}$

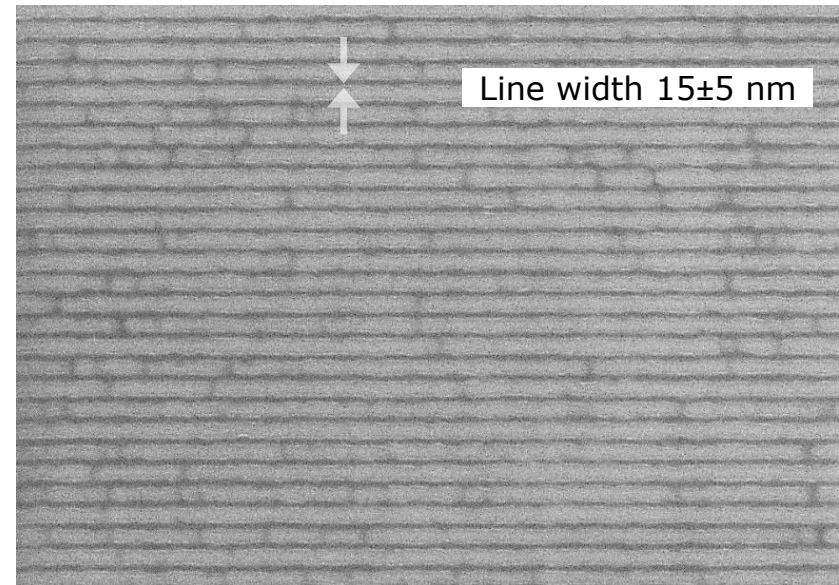
Resist: ZEP520A



Achromatic Talbot Self-Image

Half-pitch 50 nm, distance  $z \approx 50 \mu\text{m}$

Resist: ZEP520A

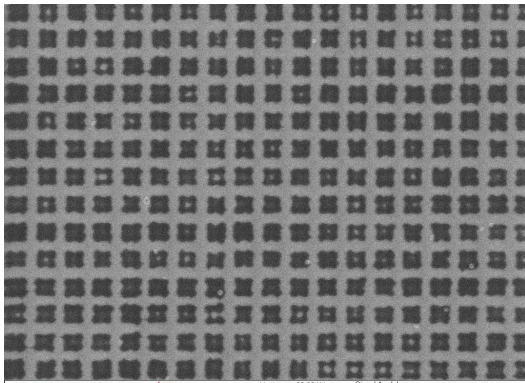


- Same lithography mask
- Pitch reduced by factor 2
- Line width reduced by factor ~10

**Exemplary application – cross-bar arrays  
for phase change memory (PCRAM)**



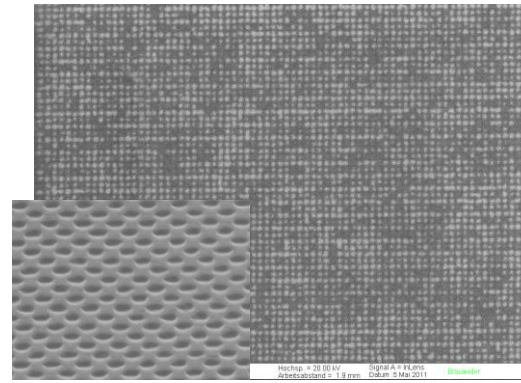
# Applications



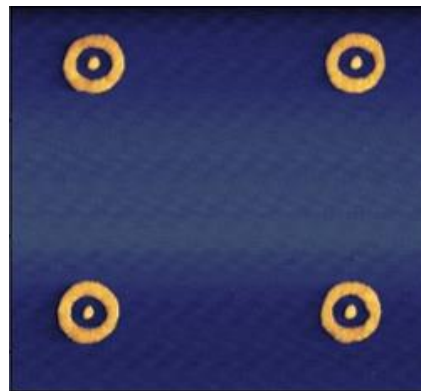
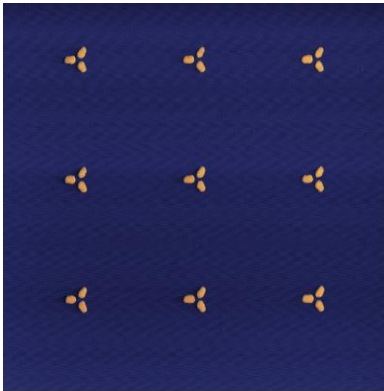
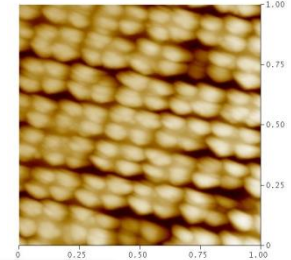
cross-bar arrays for PCRAM



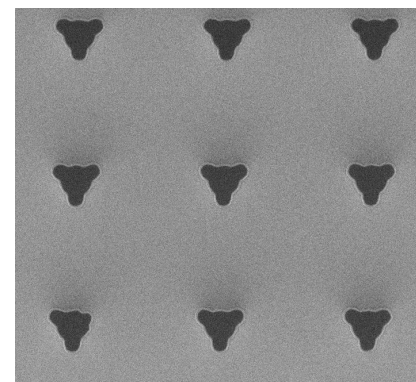
SFB 917  
**Nanoswitches**



nanodot-arrays for QD self assembly



Nanophotonic resonators



# Radiance requirement for Talbot self-imaging lithography

Mainly 0, 1<sup>st</sup> and -1<sup>st</sup> orders contribute to Talbot self-imaging effect ( $\sin \alpha_d = \lambda/d$ )

Coherence requirement depends on period  $d$  and mask to wafer distance  $g$ :

$$\theta_c \leq \frac{d}{2g}$$

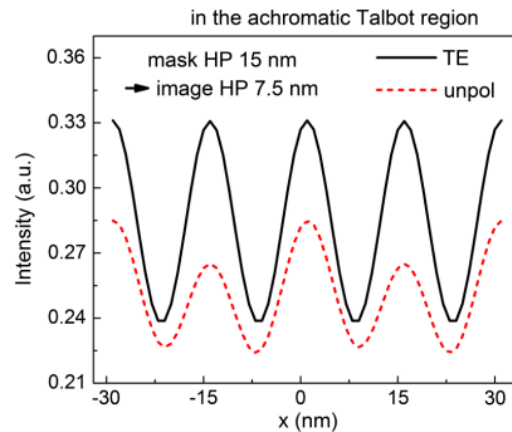
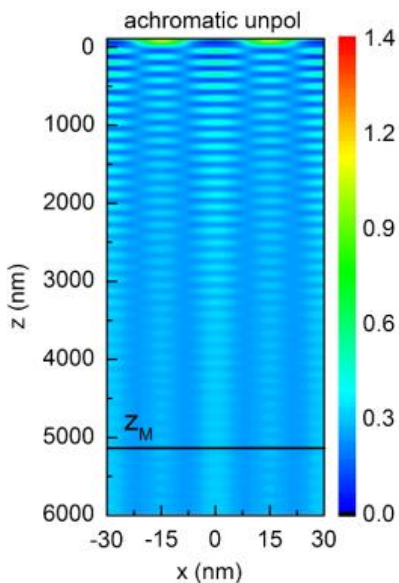
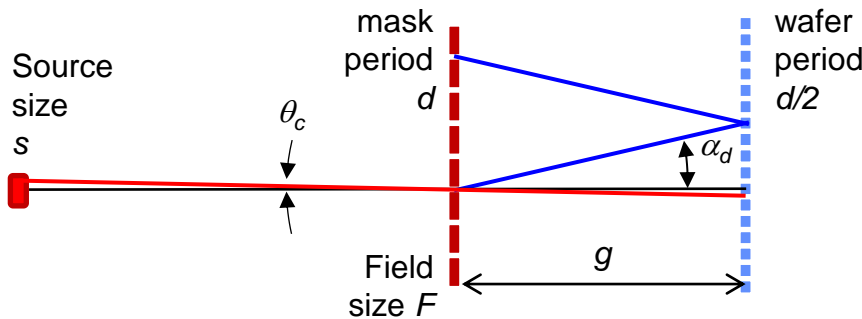
Exposure dose is determined by resist sensitivity  $D$  and  $MTF$  from mask to wafer

$$\Rightarrow L \cong \frac{D / MTF}{t_{\text{exposure}} \cdot T_{\text{system}} \cdot \Omega_{\text{illumination}}}$$

$$2d - \text{array} : \cong \frac{4 \cdot D \cdot g^2}{MTF \cdot t_{\text{exp}} \cdot d^2}$$

$$1d - \text{array} : \cong \frac{4 \cdot D \cdot g^2}{MTF \cdot t_{\text{exp}} \cdot d \cdot F}$$

implies slit-like source, alignment issue



Achromatic Talbot pattern for 15-nm half-pitch grating and cross-sections at  $g = 6 \mu\text{m}$ .

Danylyuk, Kim, et.al., J. Micro/Nanolith. MEMS MOEMS 12 (3), 033002 (2013)



## Summary – radiance requirements

EUV and soft x-ray microscopy enables imaging of nanometer sized object features with high analytical sensitivity, very good spatial resolution, and penetration depths compatible with relevant sample sizes.

Source radiance requirements are derived from the fundamental considerations of sample resolution, image contrast, detector quantum efficiency and throughput.

Photon counting is characterized by Poisson statistics. Requirement of being able to distinguish between (noisy) signal and (noisy) background results in inverse dependence of radiance on **contrast squared**.

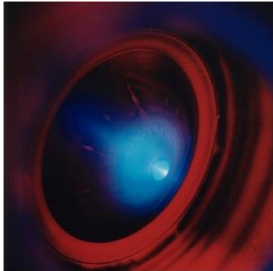
The etendue used by a high resolution EUV imaging application scales with the area of the smallest feature to be resolved or detected which is of the order of  $\lambda^2$ .

Taking into account conservation of etendue (“not compressibility” of light) and photon energy, the required radiance is proportional to  $\lambda^{-3}$ .

$$L_{source} = \frac{25 \cdot fps \cdot h \cdot c / \lambda}{c^2 \cdot T_{system} \cdot \pi \cdot NA_{illumination}^2 \cdot A_{to\ resolve\ or\ detect}}$$

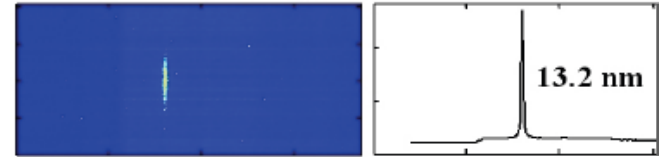
**In accessing the nano-world with laboratory imaging systems, this strong dependence implies a serious challenge for the source development.**

# Outlook



## XUV plasma based sources

- new very efficient technology
- “Aachener Lampe” successfully used in EUVL & metrology



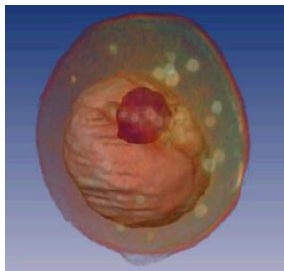
## High brilliance metrology sources

- small emitting volume
- XUV lasers



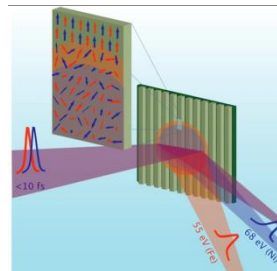
## 3d imaging

- combining of lateral and in-depth resolution
- cell nanotomography



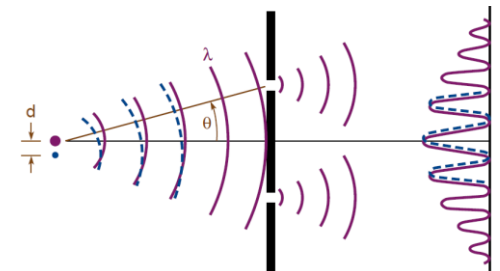
## Spectro-microscopy

- combining of spectral and lateral resolution
- magnetic domains



## Coherence

- holography
- lens less imaging
- interference litho



# Acknowledgements

EP-EUV, RWTH-Aachen, Chair for Experimental Physics of EUV

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Georg Kunkemöller, Peter Loosen, Jochen Stollenwerk, Jenny Tempeler

Fraunhofer ILT – EUV und Plasma Technology

Klaus Bergmann, Felix Küpper, Michael Scherf, Stefan Seiwert,  
Jochen Vieker, Alexander von Wezyk...

Coherent Imaging Group

John Miao, Rui Xu ...



**Fraunhofer**  
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Research  
Alliance



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FORSCHUNGSZENTRUM



Thank you very much for your attention!

